

1 exposing some portions of the layer to energy while leaving other
2 portions unexposed, the exposing altering physical properties of the
3 exposed portions relative to the unexposed portions; and

4 after the exposing, subjecting the exposed and unexposed portions
5 of the layer to common conditions, the common conditions being
6 effective to remove the silicon-comprising material and comprising a rate
7 of removal that is influenced by the altered physical properties of the
8 layer, the common conditions removing either the exposed or unexposed
9 portions faster than the other of the exposed and unexposed portions.

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11 New Claims

12 Sub 30 The method of claim 1 wherein the forming a layer
13 comprises depositing a layer of material comprising oxygen as deposited.

14 a3
15 31. The method of claim 1 wherein the forming a layer
16 comprises depositing a layer of material comprising $(\text{CH}_3)_y\text{Si}(\text{OH})_{4-y}$ as
17 deposited, with y being greater than 0 and less than 4.

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19 32. The method of claim 1 wherein the forming a layer
20 comprises depositing a layer of material comprising $\text{Si}(\text{OH})_4$ as deposited.

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22 33. The method of claim 25 wherein the forming a layer
23 comprises depositing a layer of $\text{Si}(\text{OH})_4$ as deposited.